

# BCW32LT1

## General Purpose Transistors

### NPN Silicon

#### Features

- Pb-Free Package is Available

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	32	Vdc
Collector-Base Voltage	$V_{CBO}$	32	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current – Continuous	$I_C$	100	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

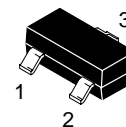
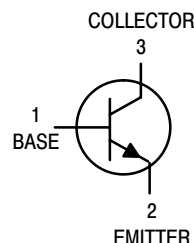
Characteristic	Symbol	Value	Unit
Total Device Dissipation FR-5 Board <sup>(1)</sup> $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, <sup>(2)</sup> $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

- FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



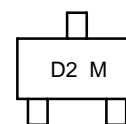
ON Semiconductor®

<http://onsemi.com>



SOT-23 (TO-236AB)  
CASE 318  
STYLE 6

#### MARKING DIAGRAM



M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping†
BCW32LT1	SOT-23	3000 Units / Reel
BCW32LT1G	SOT-23 (Pb-Free)	3000 Units / Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BCW32LT1

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mA, V <sub>EB</sub> = 0)	V <sub>(BR)CEO</sub>	32	–	–	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	32	–	–	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 μA, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	5.0	–	–	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 32 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 32 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C)	I <sub>CBO</sub>	–	–	100 10	nA μA
<b>ON CHARACTERISTICS</b>					
DC Current Gain (I <sub>C</sub> = 2.0 mA, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	200	–	450	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.5 mA)	V <sub>CE(sat)</sub>	–	–	0.25	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 2.0 mA, V <sub>CE</sub> = 5.0 Vdc)	V <sub>BE(on)</sub>	0.55	–	0.70	Vdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Output Capacitance (I <sub>E</sub> = 0, V <sub>CB</sub> = 10 Vdc, f = 1.0 MHz)	C <sub>obo</sub>	–	–	4.0	pF
Noise Figure (I <sub>C</sub> = 0.2 mA, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB

## TYPICAL NOISE CHARACTERISTICS

(V<sub>CE</sub> = 5.0 Vdc, T<sub>A</sub> = 25°C)

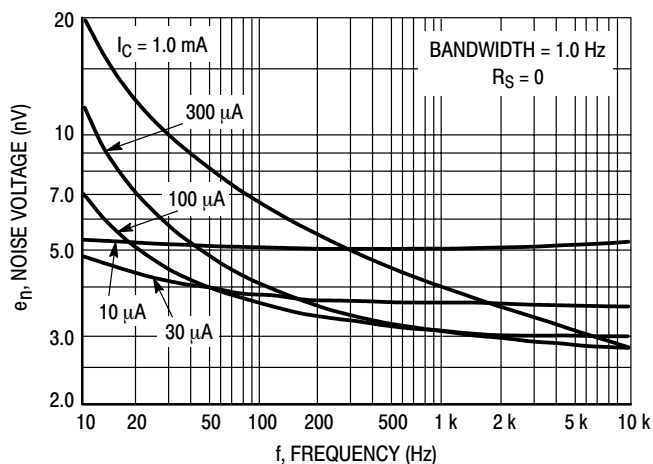


Figure 1. Noise Voltage

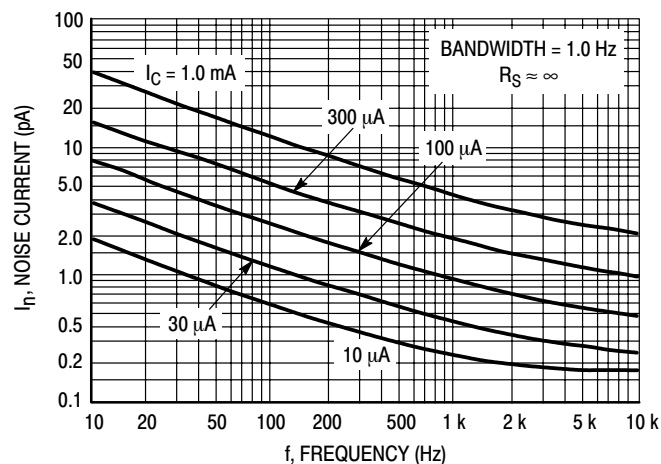


Figure 2. Noise Current

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## NOISE FIGURE CONTOURS

( $V_{CE} = 5.0 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ )

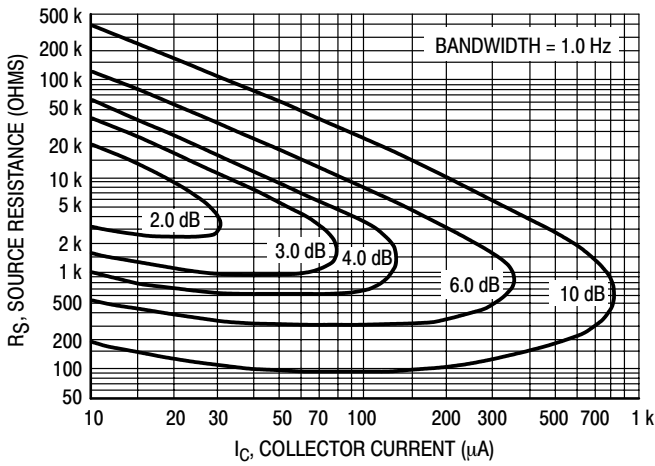


Figure 3. Narrow Band, 100 Hz

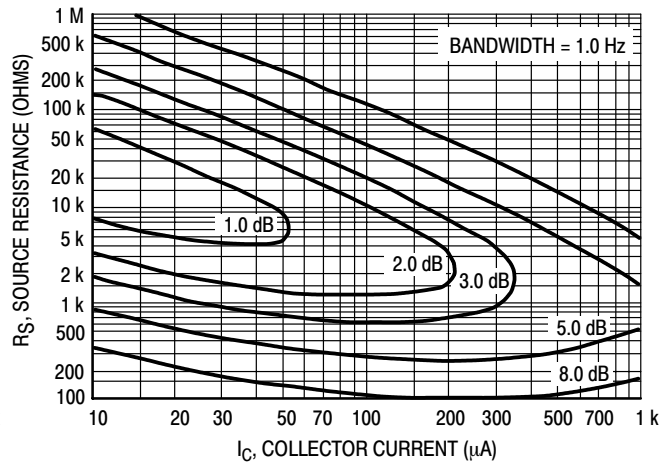


Figure 4. Narrow Band, 1.0 kHz

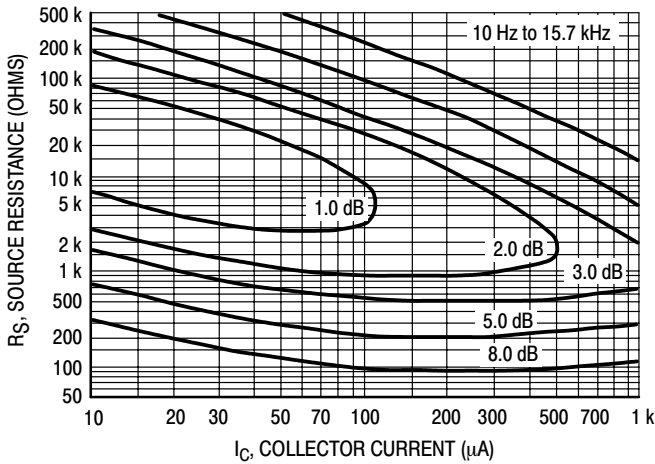


Figure 5. Wideband

Noise Figure is defined as:

$$NF = 20 \log_{10} \left( \frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right)^{1/2}$$

$e_n$  = Noise Voltage of the Transistor referred to the input. (Figure 3)

$I_n$  = Noise Current of the Transistor referred to the input.

$n$  (Figure 4)

$K$  = Boltzman's Constant ( $1.38 \times 10^{-23} \text{ J/}^\circ\text{K}$ )

$T$  = Temperature of the Source Resistance ( $^\circ\text{K}$ )

$R$  = Source Resistance ( $\Omega$ )

$S$

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## TYPICAL STATIC CHARACTERISTICS

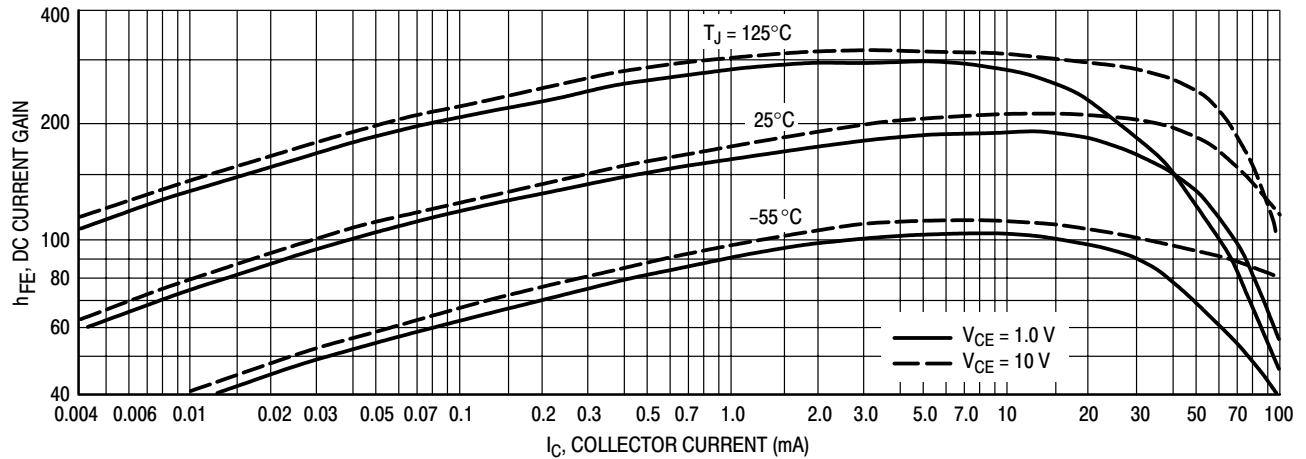


Figure 6. DC Current Gain

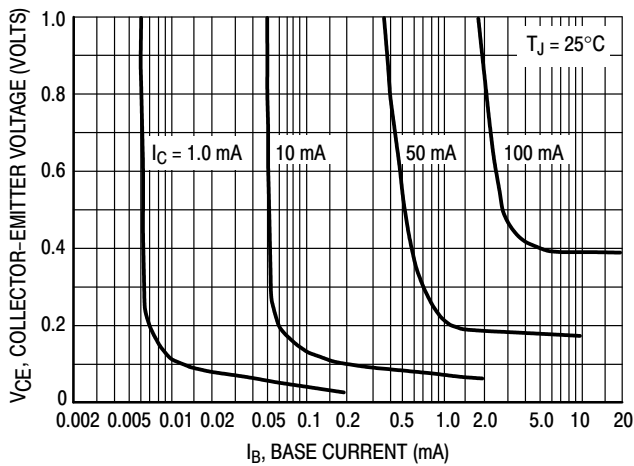


Figure 7. Collector Saturation Region

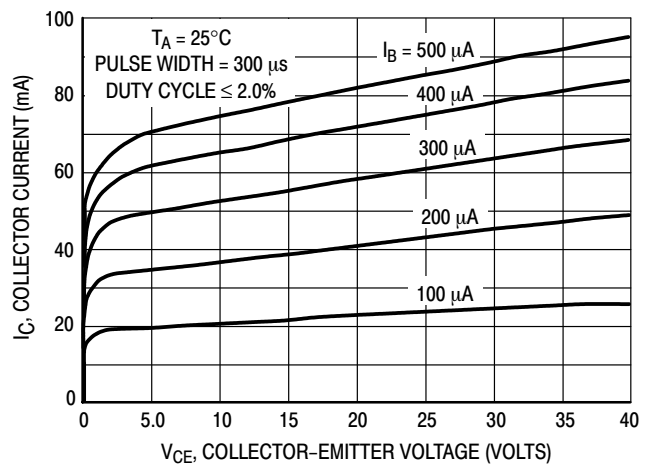


Figure 8. Collector Characteristics

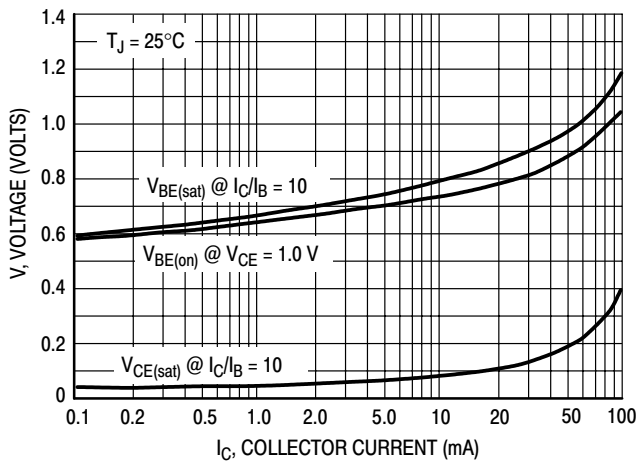


Figure 9. "On" Voltages

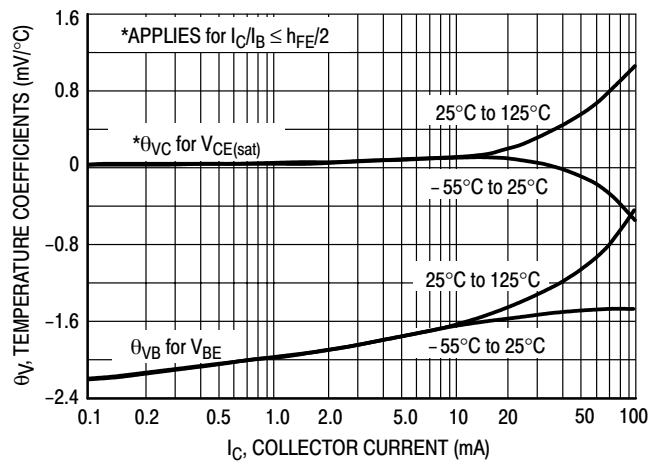


Figure 10. Temperature Coefficients

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## TYPICAL DYNAMIC CHARACTERISTICS

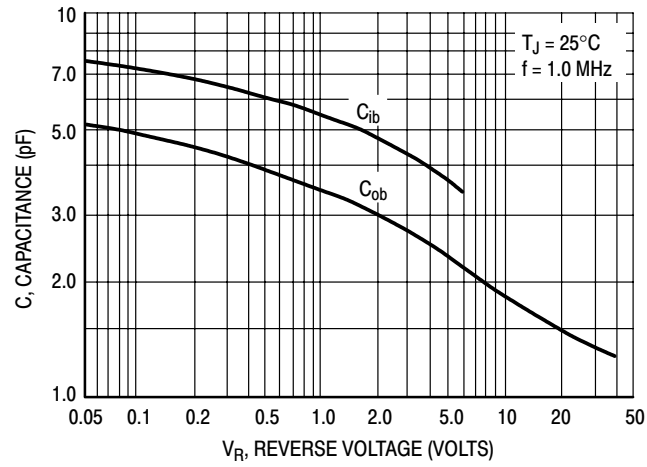


Figure 11. Capacitance

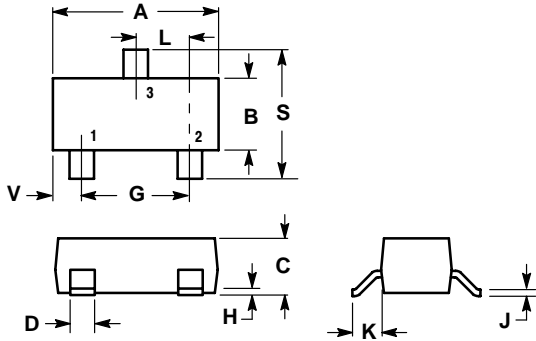
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## PACKAGE DIMENSIONS

### SOT-23 (TO-236AB)

CASE 318-08

ISSUE AK



#### NOTES:

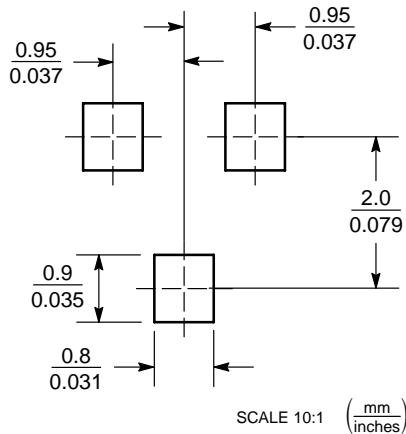
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60


#### STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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